

6A HIGH-SPEED MOSFET DRIVERS

FEATURES

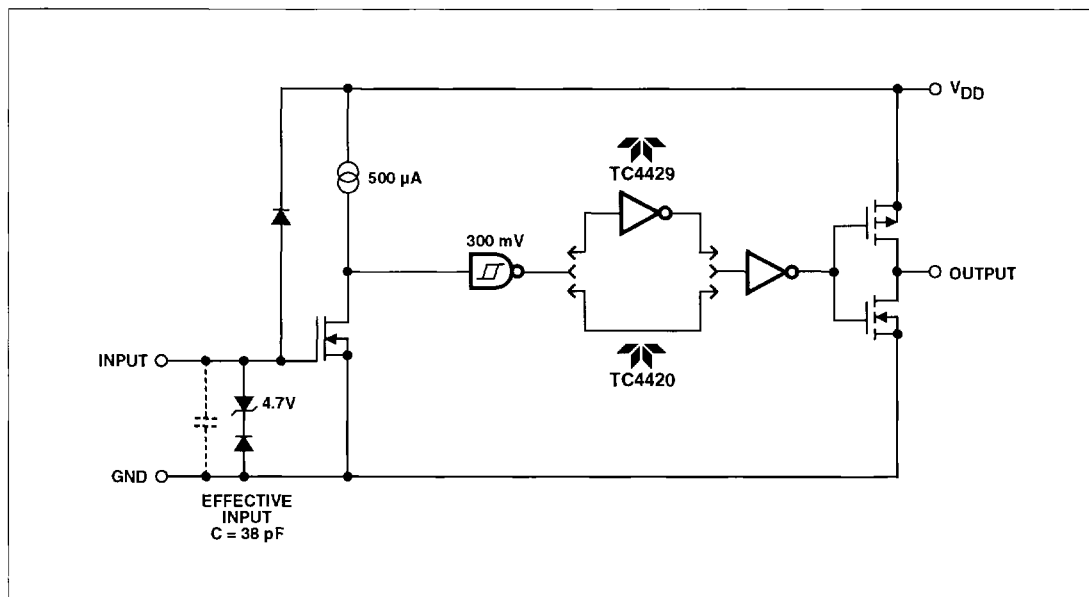
- Tough CMOS™ Construction
- Latch-Up Protected: Will Withstand >1.5A Reverse Output Current
- Logic Input Will Withstand Negative Swing Up to 5V
- ESD Protected 4 kV
- Matched Rise and Fall Times 25 ns
- High Peak Output Current 6A Peak
- Wide Operating Range 4.5V to 18V
- High Capacitive Load Drive 10,000 pF
- Low Delay Time 55 ns Typ
- Logic High Input, Any Voltage 2.4V to V_{DD}
- Low Supply Current With Logic "1" Input... 450 μ A
- Low Output Impedance..... 2.5 Ω
- Output Voltage Swing to Within 25 mV of Ground or V_{DD}

APPLICATIONS

- Switch-Mode Power Supplies
- Motor Controls
- Pulse Transformer Driver
- Class D Switching Amplifiers

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FUNCTIONAL DIAGRAM



6A HIGH-SPEED MOSFET DRIVERS

TC4420 TC4429

GENERAL DESCRIPTION

The TC4420/4429 Tough CMOS™ drivers are efficient and easy to use. These devices are 6A (peak) single output MOSFET drivers.

The TC4420/4429 will drive even the largest MOSFETs.

These devices are tough due to extra steps taken to protect them from failures. An epitaxial layer is used to prevent CMOS latch-up. Proprietary circuits allow the input to swing negative as much as 5V without damaging the part. Special circuits have been added to protect against damage from electrostatic discharge. A special molding compound is used for increased moisture resistance and ability to withstand high voltages. They are also tough

because of Teledyne Components' world-class process controls and device quality.

Because these devices are fabricated in CMOS, they run cool, use less power and are easier to drive. The rail-to-rail swing capability of CMOS better insures adequate gate voltage to the MOSFET during power up/down sequencing.

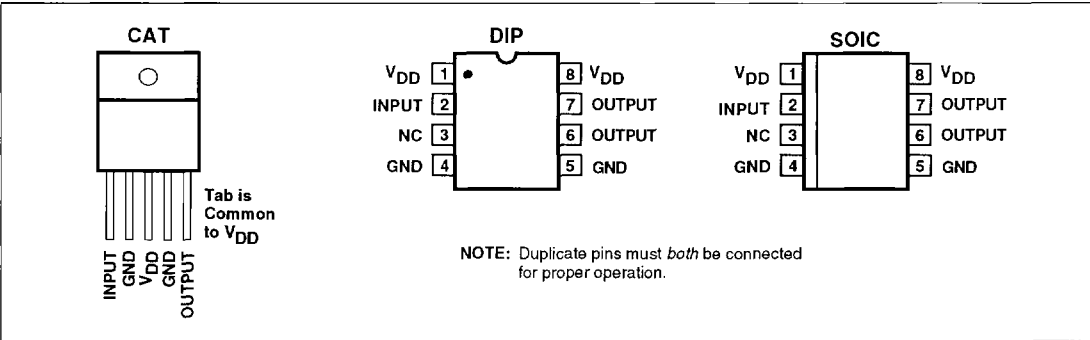
The Tough CMOS™ drivers are easy to use. Three or more discrete components can be replaced with a single device to save PCB area. Any logic input from 2.4V to V_{DD} can be used without external speed-up capacitors or resistor networks.

This family is available in inverting (TC4429) and noninverting (TC4420) configurations. The TC4429 is pin compatible with the popular TC429.

ORDERING INFORMATION

Part No.	Logic	Package	Temperature Range
TC4420CPA	Noninverting	8-Pin PDIP	0°C to +70°C
TC4420EPA	Noninverting	8-Pin PDIP	-40°C to +85°C
TC4420COA	Noninverting	8-Pin SOIC	0°C to +70°C
TC4420EOA	Noninverting	8-Pin SOIC	-40°C to +85°C
TC4420IJA	Noninverting	8-Pin CerDIP	-25°C to +85°C
TC4420MJA	Noninverting	8-Pin CerDIP	-55°C to +125°C
TC4420CAT	Noninverting	5-Pin TO-220	0°C to +70°C
TC4429CPA	Inverting	8-Pin PDIP	0°C to +70°C
TC4429EPA	Inverting	8-Pin PDIP	-40°C to +85°C
TC4429COA	Inverting	8-Pin SOIC	0°C to +70°C
TC4429EOA	Inverting	8-Pin SOIC	-40°C to +85°C
TC4429IJA	Inverting	8-Pin CerDIP	-25°C to +85°C
TC4429MJA	Inverting	8-Pin CerDIP	-55°C to +125°C
TC4429CAT	Inverting	5-Pin TO-220	0°C to +70°C

PIN CONFIGURATIONS



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ABSOLUTE MAXIMUM RATINGS

Supply Voltage	+20V
Input Voltage	−5V to V_{DD}
Input Current ($V_{IN} > V_{DD}$)	50 mA
Power Dissipation, $T_A \leq 25^\circ\text{C}$	
PDIP	1W
SOIC	500 mW
CerDIP	800 mW
5-Pin TO-220	1.5W
Power Dissipation, $T_C \leq 25^\circ\text{C}$	
5-Pin TO-220	12.5W
Derating Factors (To Ambient)	
PDIP	8 mW/ $^\circ\text{C}$
SOIC	4 mW/ $^\circ\text{C}$
CerDIP	6.4 mW/ $^\circ\text{C}$
5-Pin TO-220	12 mW/ $^\circ\text{C}$
Thermal Impedances (To Case)	
5-Pin TO-220 $R_{\theta JA}$	10 $^\circ\text{C/W}$

Storage Temperature Range	−55 $^\circ\text{C}$ to +150 $^\circ\text{C}$
Operating Temperature (Chip)	+150 $^\circ\text{C}$
Operating Temperature Range (Ambient)	
C Version	0 $^\circ\text{C}$ to +70 $^\circ\text{C}$
I Version	−25 $^\circ\text{C}$ to +85 $^\circ\text{C}$
E Version	−40 $^\circ\text{C}$ to +85 $^\circ\text{C}$
M Version	−55 $^\circ\text{C}$ to +125 $^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)	+300 $^\circ\text{C}$

Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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ELECTRICAL CHARACTERISTICS: $T_A = +25^\circ\text{C}$ with $4.5\text{V} \leq V_{DD} \leq 18\text{V}$, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Input						
V_{IH}	Logic 1 High Input Voltage		2.4	1.8	—	V
V_{IL}	Logic 0 Low Input Voltage		—	1.3	0.8	V
$V_{IN}(\text{Max})$	Input Voltage Range		−5	—	$V_{DD}+0.3$	V
I_{IN}	Input Current	$0\text{V} \leq V_{IN} \leq V_{DD}$	−10	—	10	μA
Output						
V_{OH}	High Output Voltage	See Figure 1	$V_{DD}-0.025$	—	—	V
V_{OL}	Low Output Voltage	See Figure 1	—	—	0.025	V
R_O	Output Resistance, High	$I_{OUT} = 10\text{ mA}$, $V_{DD} = 18\text{V}$	—	2.1	2.8	Ω
R_O	Output Resistance, Low	$I_{OUT} = 10\text{ mA}$, $V_{DD} = 18\text{V}$	—	1.5	2.5	Ω
I_{PK}	Peak Output Current	$V_{DD} = 18\text{V}$ (See Figure 5)	—	6	—	A
I_{REV}	Latch-Up Protection Withstand Reverse Current	Duty Cycle $\leq 2\%$ $t \leq 300\text{ }\mu\text{s}$	>1.5	—	—	A
Switching Time (Note 1)						
t_R	Rise Time	Figure 1, $C_L = 2500\text{ pF}$	—	25	35	ns
t_F	Fall Time	Figure 1, $C_L = 2500\text{ pF}$	—	25	35	ns
t_{D1}	Delay Time	Figure 1	—	55	75	ns
t_{D2}	Delay Time	Figure 1	—	55	75	ns
Power Supply						
I_S	Power Supply Current	$V_{IN} = 3\text{V}$	—	0.45	1.5	mA
		$V_{IN} = 0\text{V}$	—	55	150	μA
V_{DD}	Operating Input Voltage		4.5	—	18	V

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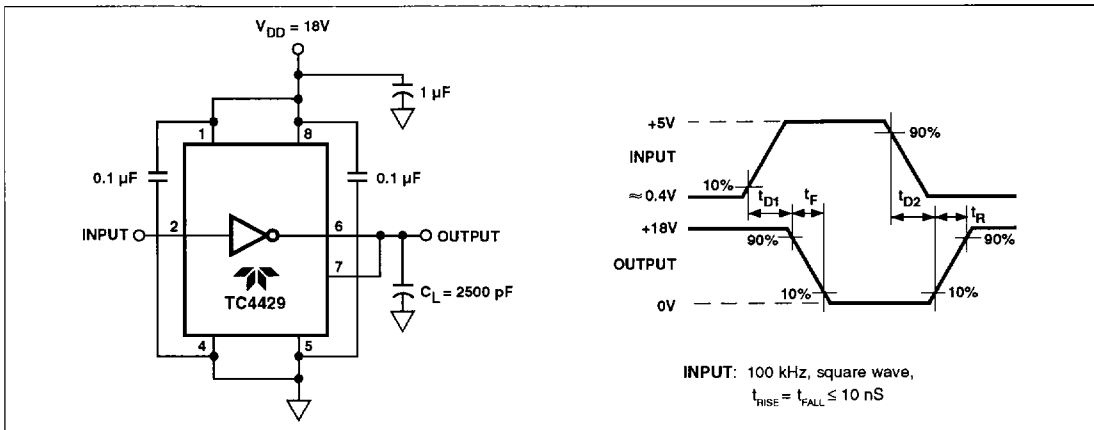
TC4420 TC4429

ELECTRICAL CHARACTERISTICS:

Measured over operating temperature range with $4.5V \leq V_{DD} \leq 18V$, unless otherwise specified.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Input						
V_{IH}	Logic 1 High Input Voltage		2.4	—	—	V
V_{IL}	Logic 0 Low Input Voltage		—	—	0.8	V
$V_{IN} (Max)$	Input Voltage Range		-5	—	$V_{DD}+0.3$	V
I_{IN}	Input Current	$0V \leq V_{IN} \leq V_S$	-10	—	10	μA
Output						
V_{OH}	High Output Voltage	See Figure 1	$V_{DD}-0.025$	—	—	V
V_{OL}	Low Output Voltage	See Figure 1	—	—	0.025	V
R_O	Output Resistance, High	$I_{OUT} = 10 \text{ mA}$, $V_{DD} = 18V$	—	3	5	Ω
R_O	Output Resistance, Low	$I_{OUT} = 10 \text{ mA}$, $V_{DD} = 18V$	—	2.3	5	Ω
Switching Time (Note 1)						
t_R	Rise Time	Figure 1, $C_L = 2500 \text{ pF}$	—	32	60	ns
t_F	Fall Time	Figure 1, $C_L = 2500 \text{ pF}$	—	34	60	ns
t_{D1}	Delay Time	Figure 1	—	50	100	ns
t_{D2}	Delay Time	Figure 1	—	65	100	ns
Power Supply						
I_S	Power Supply Current	$V_{IN} = 3V$	—	0.45	3	mA
		$V_{IN} = 0V$	—	60	400	μA
V_{DD}	Operating Input Voltage		4.5	—	18	V

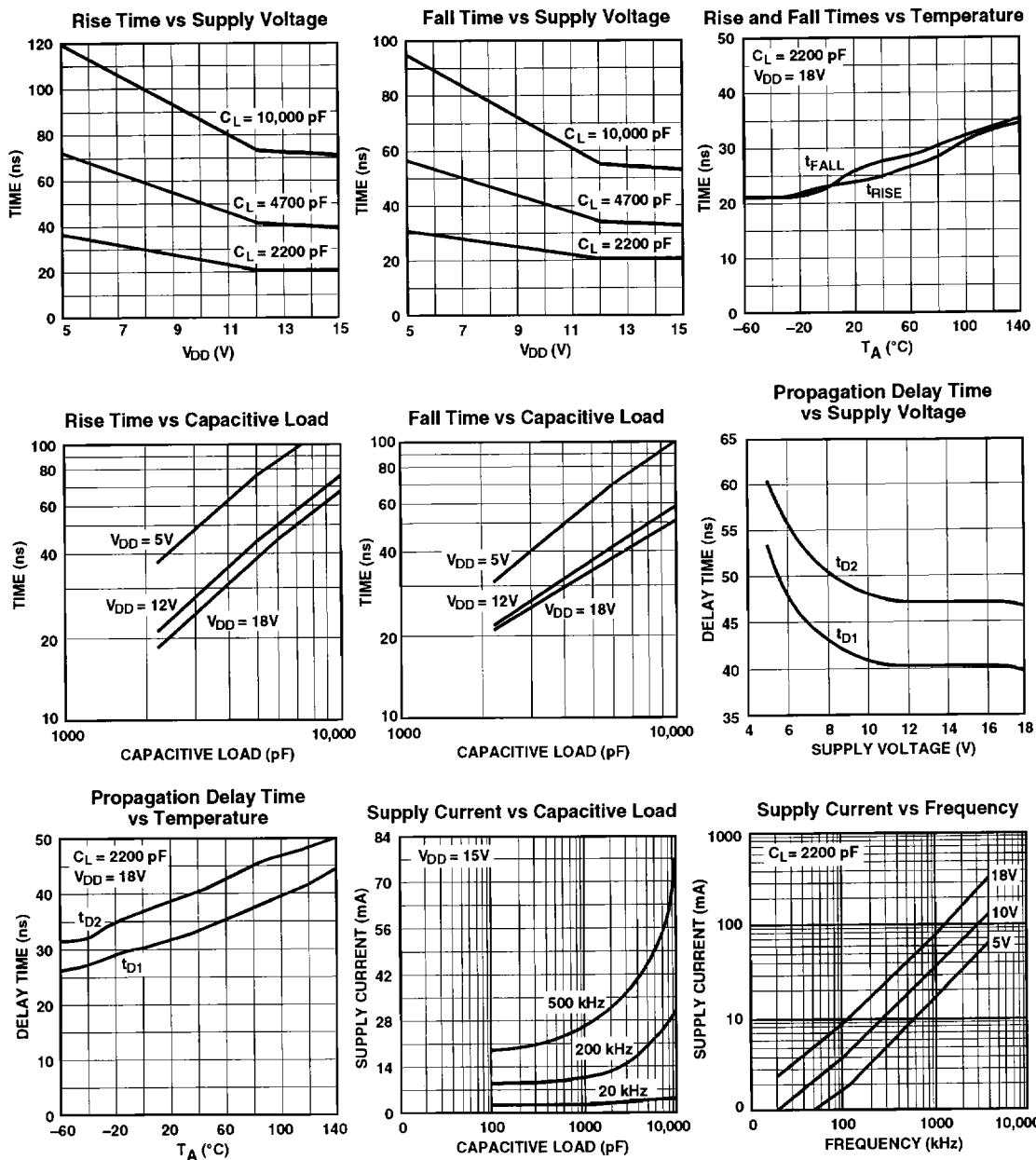
NOTE: 1. Switching times guaranteed by design.



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TYPICAL CHARACTERISTICS CURVES

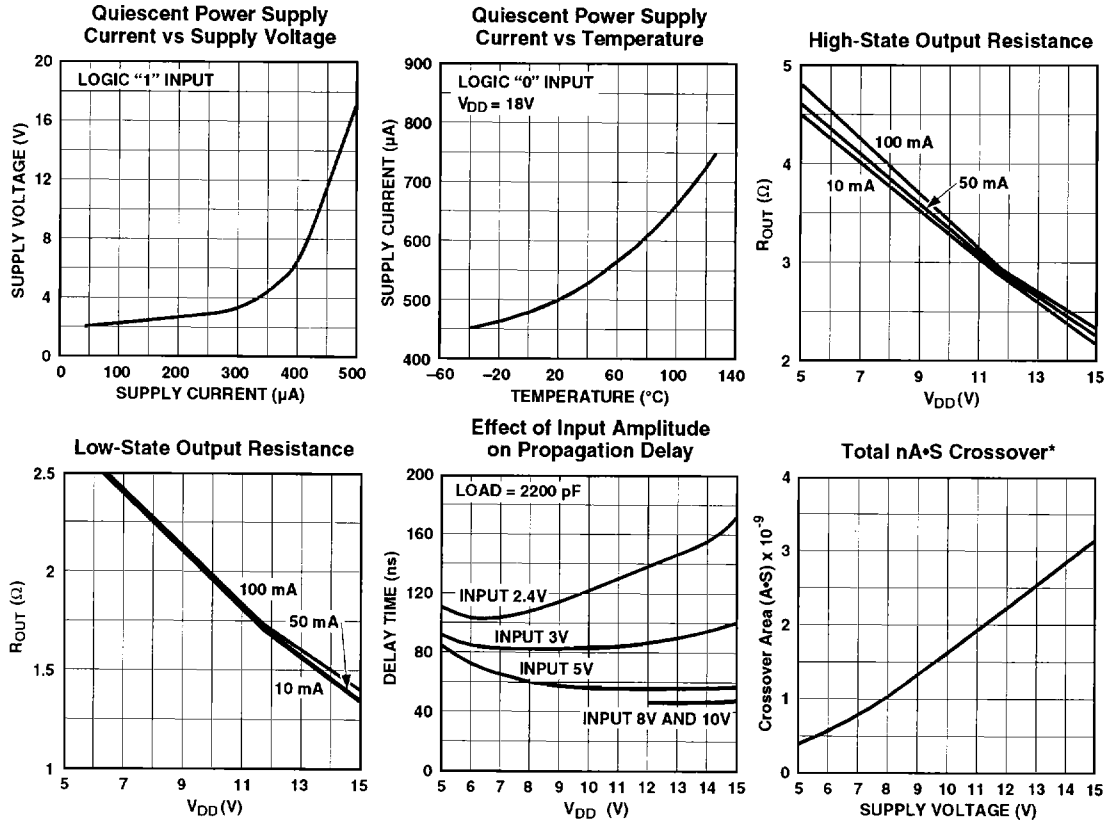


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TYPICAL CHARACTERISTICS CURVES (Cont.)



* The values on this graph represent the loss seen by the driver during one complete cycle. For a single transition, divide the value by 2.

BONDING DIAGRAM

